

## Features

- 40V/210A,  
 $R_{DS(ON)} = 1.9m\Omega(Typ.)@V_{GS}=10V$
- Low  $R_{DS(ON)}$
- Super High Dense Cell Design
- Fast Recovery Body Diode
- 100% Avalanche Tested

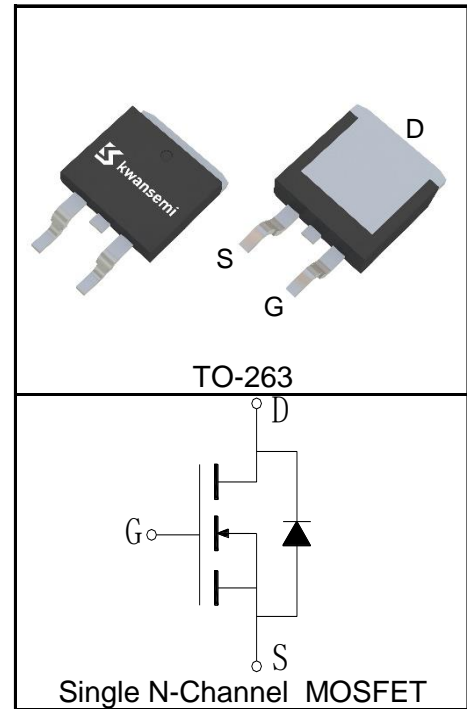
## Applications

- Synchronous Rectification
- UPS Inverter
- High efficiency DC/DC Converters



Halogen-Free

## Pin Description



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
<b>Common Ratings</b> ( $T_C=25^\circ\text{C}$ Unless Otherwise Noted)			
$V_{DSS}$	Drain-Source Voltage	40	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	
$T_{Jmax}$	Maximum Junction Temperature	175	$^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to 175	$^\circ\text{C}$
$I_S$	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 210	A
<b>Mounted on Large Heat Sink</b>			
$I_{DP}^{①}$	300 $\mu\text{s}$ Pulse Drain Current Tested	$T_C=25^\circ\text{C}$ 840	A
$I_D^{②}$	Continuous Drain Current( $V_{GS}=10V$ )	$T_C=25^\circ\text{C}$ 210	A
		$T_C=100^\circ\text{C}$ 148	
$P_D$	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 200	W
		$T_C=100^\circ\text{C}$ 100	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	0.75	$^\circ\text{C}/\text{W}$
$R_{\theta JA}^{③}$	Thermal Resistance-Junction to Ambient	62.5	$^\circ\text{C}/\text{W}$
<b>Drain-Source Avalanche Ratings</b>			
$E_{AS}^{④}$	Avalanche Energy, Single Pulsed	1156	mJ

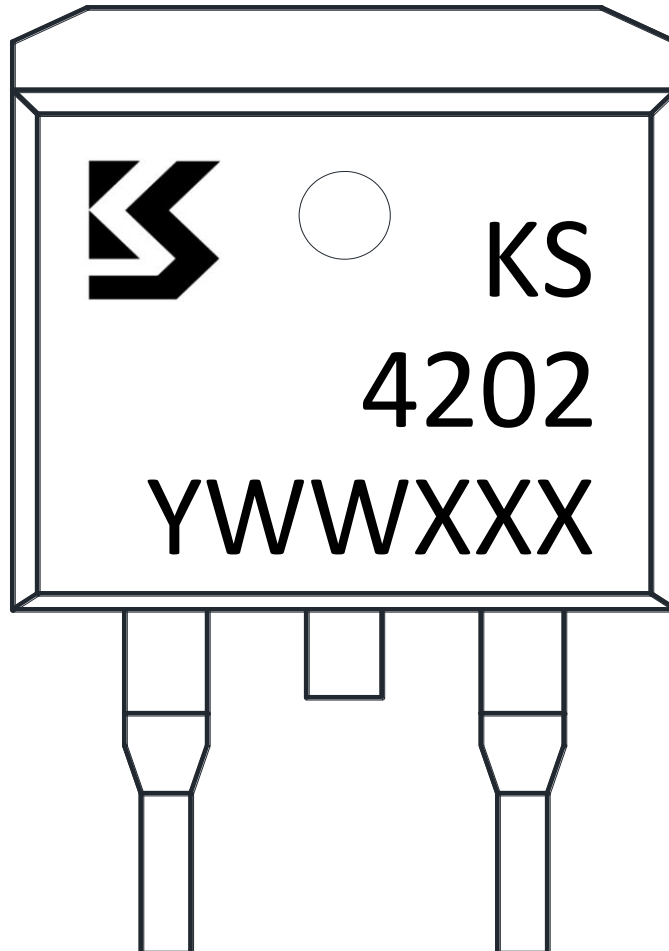
**Electrical Characteristics** ( $T_C=25^\circ\text{C}$  Unless Otherwise Noted)

Symbol	Parameter	Test Condition	KS4202GA			Unit
			Min.	Typ.	Max.	
<b>Static Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	40			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=40V, V_{GS}=0V$			5	$\mu A$
		$T_J=125^\circ\text{C}$			100	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2	3	4	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 100$	nA
$R_{DS(ON)}^{(5)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=80A$		1.9	2.4	m $\Omega$
<b>Diode Characteristics</b>						
$V_{SD}^{(5)}$	Diode Forward Voltage	$I_{SD}=80A, V_{GS}=0V$		0.88	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_{SD}=80A, dI_{SD}/dt=100A/\mu s$		77		ns
$Q_{rr}$	Reverse Recovery Charge			53		nC
<b>Dynamic Characteristics</b> <sup>⑥</sup>						
$R_G$	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$		1.3		$\Omega$
$C_{iss}$	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=20V,$ Frequency=1.0MHz		8070		pF
$C_{oss}$	Output Capacitance			795		
$C_{rss}$	Reverse Transfer Capacitance			645		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=20V, I_{DS}=80A,$ $V_{GEN}=10V, R_G=2.5\Omega$		19		ns
$t_r$	Turn-on Rise Time			67		
$t_{d(OFF)}$	Turn-off Delay Time			49		
$t_f$	Turn-off Fall Time			31		
<b>Gate Charge Characteristics</b> <sup>⑥</sup>						
$Q_g$	Total Gate Charge	$V_{DS}=20V, V_{GS}=10V,$ $I_{DS}=80A$		146		nC
$Q_{gs}$	Gate-Source Charge			41		
$Q_{gd}$	Gate-Drain Charge			49		

- Notes:
- ① Pulse width limited by safe operating area.
  - ② Calculated continuous current based on maximum allowable junction temperature. The package limitation current is 75A.
  - ③ When mounted on 1 inch square copper board,  $t \leq 10\text{sec}$ . The value in any given application depends on the user's specific board design.
  - ④ Limited by  $T_{Jmax}$ , Starting  $T_J = 25^\circ\text{C}$ ,  $I_{ASmax} = 68A$ ,  $L = 0.5\text{mH}$ ,  $V_{DD} = 40V$ ,  $R_G = 25\Omega$ ,  $V_{GS} = 10V$ . Part not recommended for use above this value. 100% Final Test at  $I_{AS} = 50A$ ,  $L = 0.5\text{mH}$ .
  - ⑤ Pulse test; Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
  - ⑥ Guaranteed by design, not subject to production testing.

**Ordering and Marking Information**

Device	Package	Packaging	Quantity	Reel Size	Tape width
KS4202GA	TO-263	Tape&Reel	800	13"	24mm

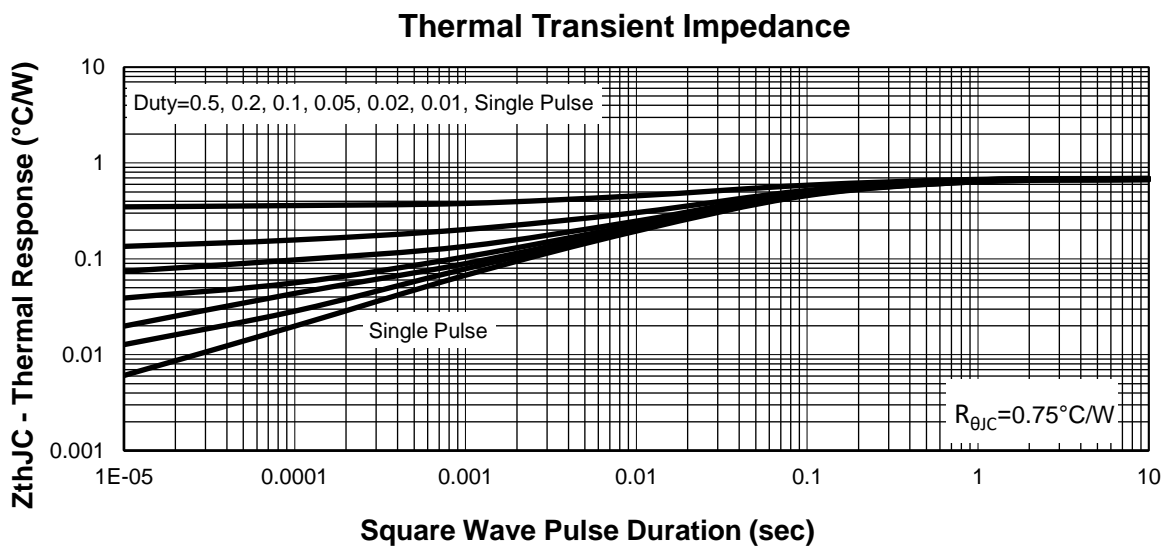
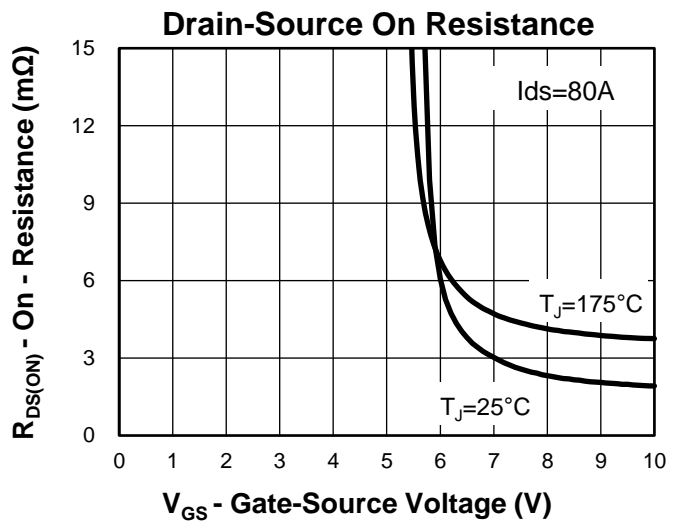
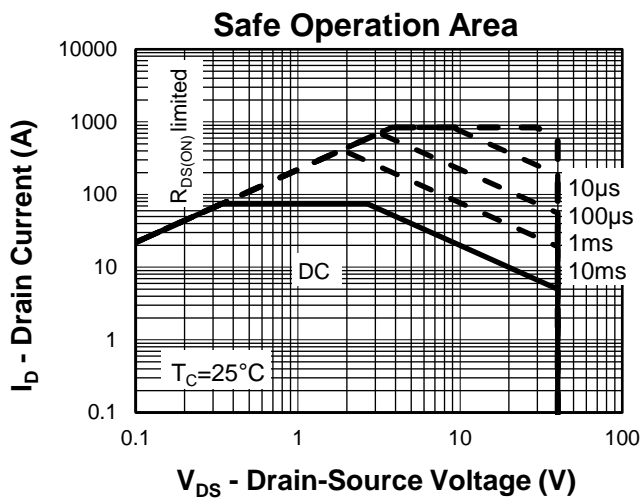
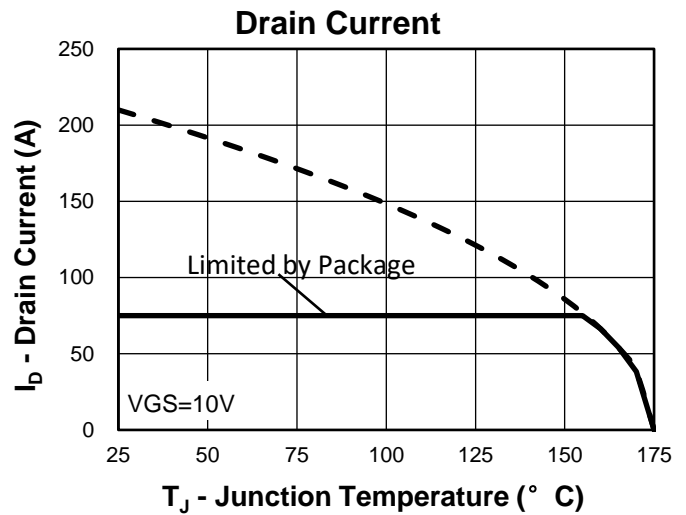
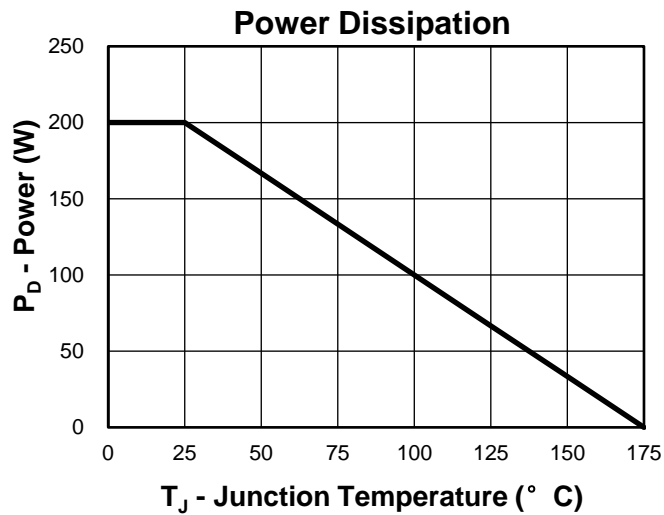


1st Line: Kwansemi LOGO, Kwansemi Code(KS)

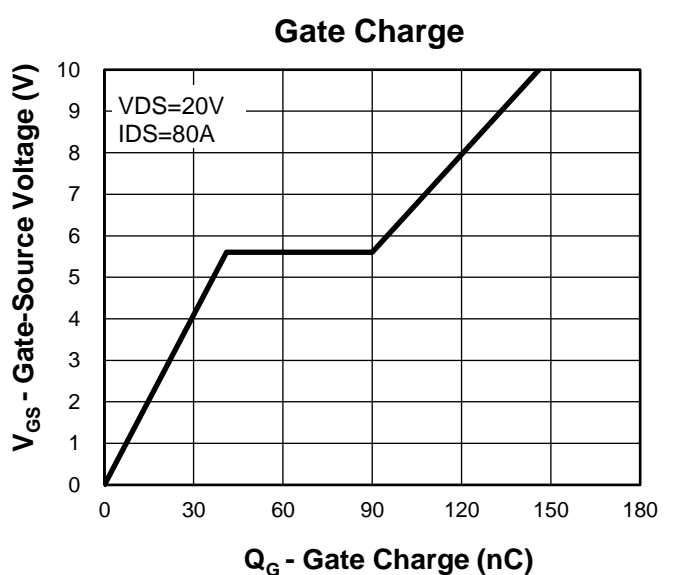
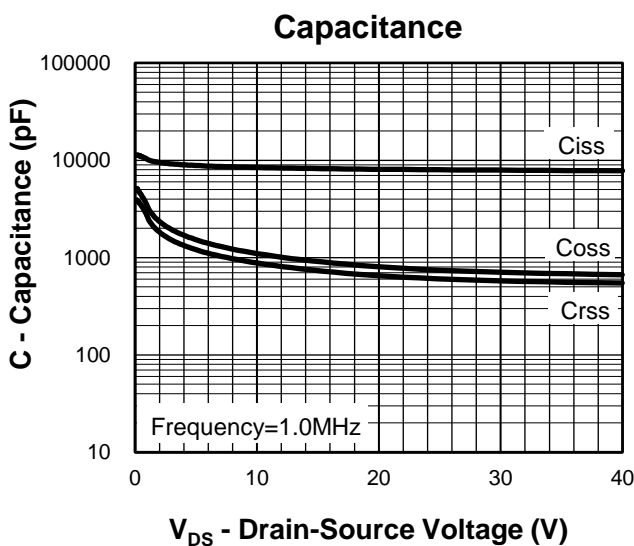
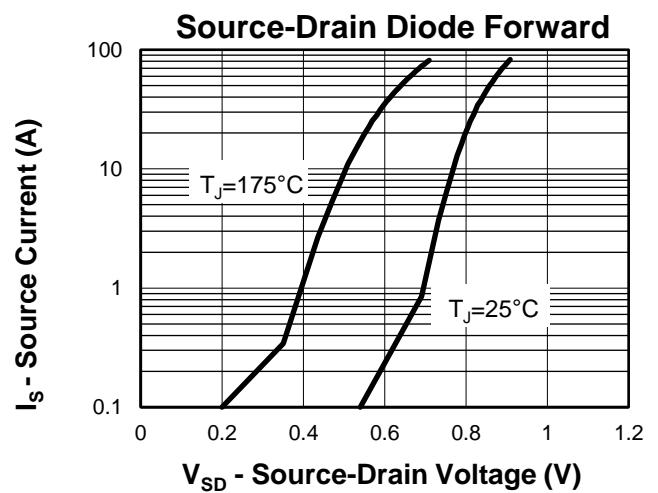
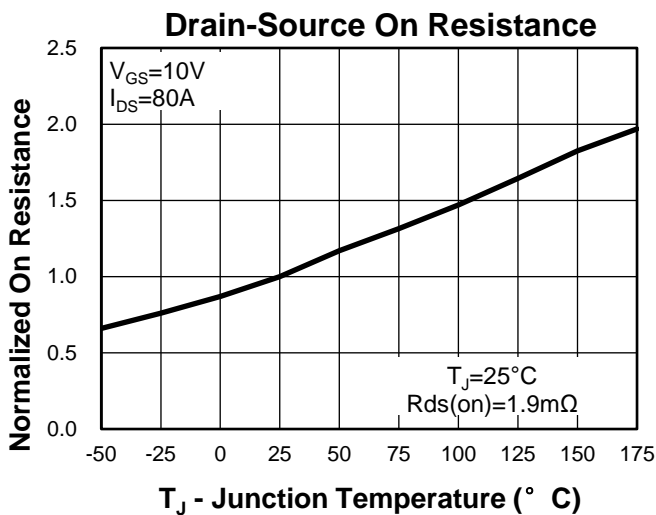
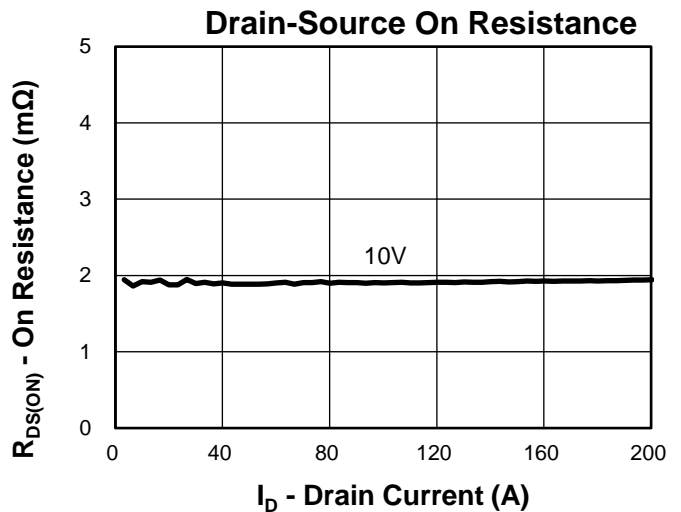
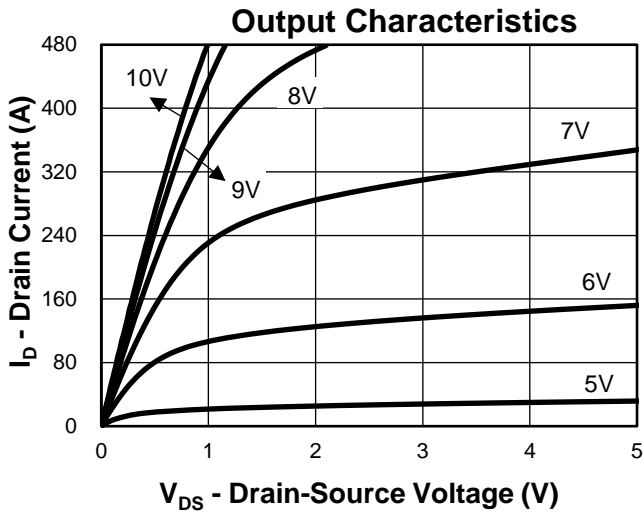
2nd Line: Part Number(4202)

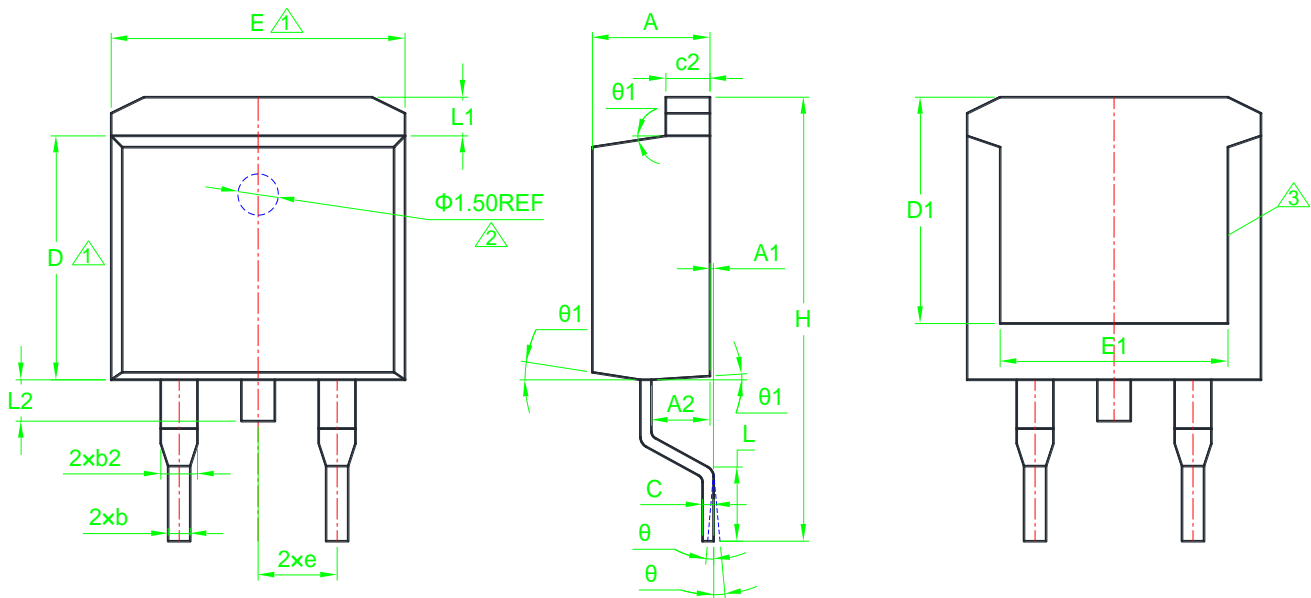
3rd Line: Lot Number(YWWXXX)

### Typical Characteristics



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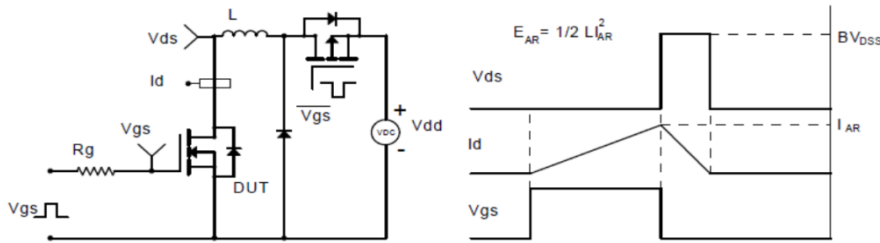


**Package Information**
**TO-263**


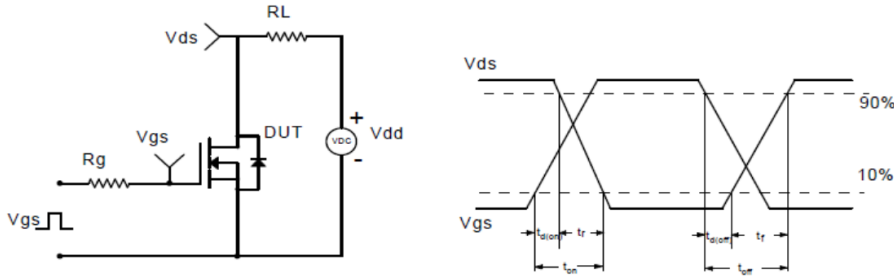
SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.30	4.50	4.80	0.169	0.177	0.189	e	2.54BSC			0.100BSC		
A1	0.00	0.10	0.25	0.000	0.004	0.010	E	9.90	10.10	10.30	0.390	0.398	0.406
A2	2.20	*	2.80	0.087	*	0.110	E1	7.00	*	8.50	0.276	*	0.335
b	0.70	0.85	0.95	0.028	0.033	0.037	H	14.80	*	15.70	0.583	*	0.618
b2	1.15	*	1.47	0.045	*	0.058	L	2.10	*	2.79	0.083	*	0.110
c	0.38	*	0.65	0.015	*	0.026	L1	1.10	*	1.42	0.043	*	0.056
c2	1.20	1.30	1.40	0.047	0.051	0.055	L2	1.00	*	1.70	0.039	*	0.067
D	8.40	8.90	9.40	0.331	0.350	0.370	theta	0°	*	8°	0°	*	8°
D1	7.10	*	8.20	0.280	*	0.323	theta 1	3°	*	9°	3°	*	9°

- ① Dimensions D and E do not include mold flash protrusions or gate burrs.
- ② The existence and size of demolding hole are variable depending on mold.
- ③ The size and shape of exposed pad are variable depending on mold.

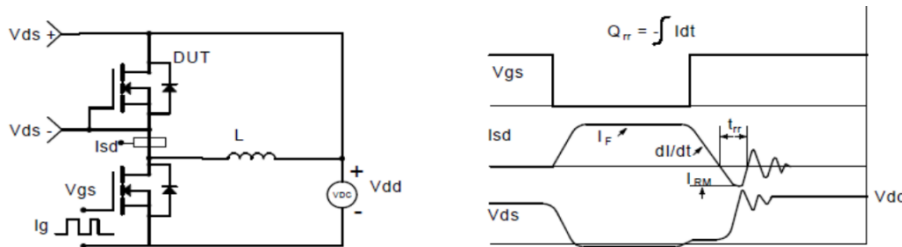
**Avalanche Test Circuit and Waveforms**



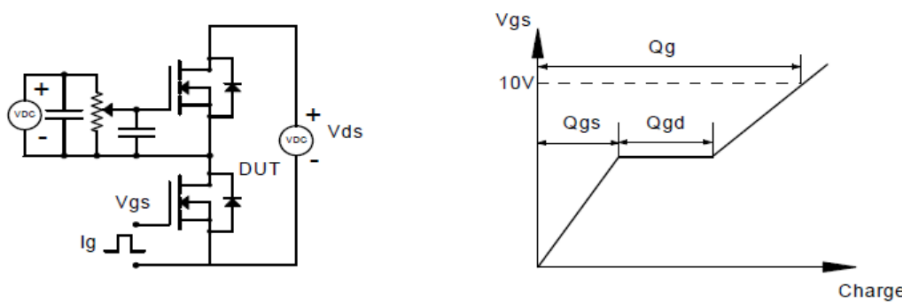
**Switching Time Test Circuit and Waveforms**



**Diode Recovery Test Circuit and Waveforms**



**Gate Charge Test Circuit and Waveform**



**Customer Service**

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